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XRD87L85



Low-Voltage CMOS 8-Bit High-Speed Analog-to-Digital Converter

April 2002-1

FEATURES

8-Bit Resolution

• Up to 10 MHz Sampling Rate

Internal S/H Function

Single Supply: 3.3V

VIN DC Range: 0V to V_{DD}
VREF DC Range: 1V to V_{DD}

• Low Power: 25mW typ. (excluding reference)

• Latch-Up Free

ESD Protection: 2000V Minimum

20-Pin Package Available: XRD87L75

APPLICATIONS

Digital Color Copiers

Cellular Telephones

• CCDs and Scanners

Video Capture Boards

GENERAL DESCRIPTION

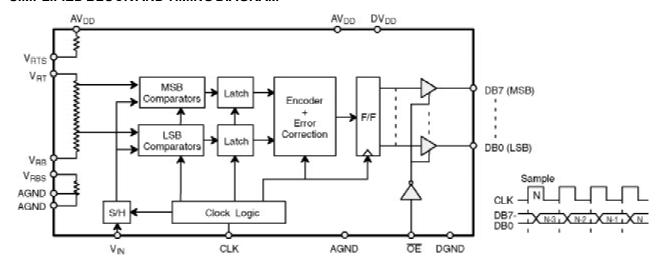
The XRD87L85 is an 8-bit Analog-to-Digital Converter. Designed using an advanced 3.3V CMOS process, this part offers excellent performance, low power consumption, and latch-up free operation.

This device uses a two-step flash architecture to maintain low power consumption at high conversion rates. The input circuitry of the XRD87L85 includes an on-chip S/H function which allows the user to digitize analog input signals between AGND and $\text{AV}_{\text{DD}}.$ Careful design and chip layout have achieved a low analog input capacitance. This reduces "kickback" and eases the requirements of the buffer/amplifier used to drive the XRD87L85. The designer can choose the internally generated reference voltages by connecting V_{RB} to

 V_{RBS} and V_{RT} to V_{RTS} , or provide external reference voltages to the V_{RB} and V_{RT} pins. The internal reference generates 0.4V at V_{RB} and 1.72V at V_{RT} . Providing external reference voltages allows easy interface to any input signal range between AGND and AV_{DD}. This also allows the system to adjust these voltages to cancel zero scale and full scale errors, or to change the input range as needed.

The device operates from a single +3.3V supply. Power consumption is 25mW at FS = 6MHz. Specified for operation over the commercial/industrial (-40 to +85°C) temperature range, the XRD87L85 is available in Plastic Dual-in-line (PDIP), Surface Mount (SOIC) and Small Outline (SOP) packages in EIAJ and JEDEC.

SIMPLIFIED BLOCK AND TIMING DIAGRAM



Rev. 1.00

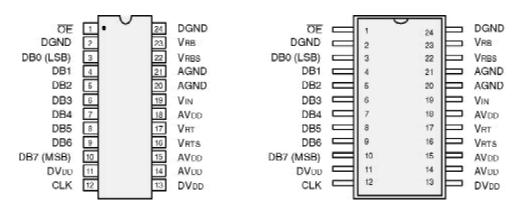


ORDERING INFORMATION

Package Type	Temperature Range	Part No.	DNL (LSB)	INL (LSB)
SOIC (Jedec)	−40 to +85°C	XRD87L85AID	+/- 0.5	+/-1.5
SOP (EIAJ)	−40 to +85°C	XRD87L85AIK	+/- 0.5	+/-1.5
Plastic Dip (300MIL)	−40 to +85°C	XRD87L85AIP	+/- 0.5	+/-1.5

PIN CONFIGURATIONS

See Packaging Section for Package Dimensions



24-Pin PDIP (300 MIL) - P24

24-Pin SOP (EIAJ, 5.4mm) – K24 24-Pin SOIC (Jedec, 300 MIL) – D24

PIN OUT DEFINITIONS

PIN NO.	NAME	DESCRIPTION	PIN NO.	NAME	DESCRIPTION
1	ŌĒ	Output Enable	13	DV_{DD}	Digital Power Supply
2	DGND	Digital Ground	14	$AV_{\mathtt{DD}}$	Analog Power Supply
3	DB0	Data Output Bit 0 (LSB)	15	$AV_{\mathtt{DD}}$	Analog Power Supply
4	DB1	Data Output Bit 1	16	V_{RTS}	Generates 1.72 V if tied to $V_{\rm RT}$
5	DB2	Data Output Bit 2	17	V_{RT}	Top Reference
6	DB3	Data Output Bit 3	18	AV_{DD}	Analog Power Supply
7	DB4	Data Output Bit 4	19	VIN	Analog Input
8	DB5	Data Output Bit 5	20	AGND	Analog Ground
9	DB6	Data Output Bit 6	21	AGND	Analog Ground
10	DB7	Data Output Bit 7 (MSB)	22	V _{RBS}	Generates 0.4 V if tied to V _{RB}
11	DV_{DD}	Digital Power Supply	23	V_{RB}	Bottom Reference
12	CLK	Sampling Clock Input	24	DGND	Digital Ground



ELECTRICAL CHARACTERISTICS TABLE

UNLESS OTHERWISE SPECIFIED: $AV_{DD} = DV_{DD} = 3.3V$, FS = 6MHz (50% DUTY CYCLE),

 $V_{RT} = 2.5V, V_{RB} = 0.5V, T_A = 25^{\circ}C$

			25°C			
Parameter	Symbol	Min	Тур	Max	Units	Test Conditions/Comments
KEYFEATURES						
Resolution		8			Bits	
Sampling Rate	FS	0.1	6	10	MHz	
ACCURACY						
Differential Non-Linearity	DNL		+/-0.3	+/-0.5	LSB	
Integral Non-Linearity	INL		+/-0.75	+/-1.5	LSB	Best Fit Line
						(Max INL – Min INL)/2
Zero Scale Error	EZS		+3		LSB	
Full Scale Error	EFS		-2		LSB	
REFERENCEVOLTAGES						
Positive Ref. Voltage	$V_{\rm RT}$		2.5	AV_{DD}	٧	
Negative Ref. Voltage	V _{RB}	AGND	0.5	55	٧	
Differential Ref. Voltage ³	V _{REF}	1.0		$AV_{\mathtt{DD}}$	V	$V_{REF} = V_{RT} - V_{RB}$
Ladder Resistance	R _L	245	350	550	Ω	ner HI HD
Ladder Temp. Coefficient	R _{TCO}	2.0	2000	000	ppm/°C	
Self Bias 1	. 100		2000		pp, 0	
Short V _{BB} and V _{BBS}	V _{RB}		0.4		V	
Short V _{RT} and V _{RTS}	V _{RT} -V _{RB}		1.72		V	
Self Bias 2	- HI - HB					
V _{BB} = AGND,	V_{RT}		1.5		V	
Short V _{RT} and V _{RTS}	- HI					
ANALOGINPUT						
Input Bandwidth (-1 dB) ^{2,4}	BW		50		MHz	
Input Voltage Range	V _{IN}	V_{RB}		V_{RT}	٧	
Input Capacitance 5	C _{IN}	no	16	NI	pF	
Aperture Delay ²	t _{AP}		4		ns	
DIGITAL INPUTS	AP					
Logical "1" Voltage	V _{IH}	2.5			V	
Logical "0" Voltage	V _{IL}	2.0		0.5	V	
DC Leakage Current 6	I _{IN}			0.0	`	V _{IN} =DGND to DV _{DD}
CLK	, IN		5		μА	V _{IN} -Band to B V _{DD}
OE			5		μΑ	
Input Capacitance			5		pF	
Clock Timing (See Figure 1.)7					F-	
Clock Period	1/FS	100	166		ns	
High Pulse Width	t _{PWH}	50	83		ns	
Low Pulse Width	t _{PWL}	50	83		ns	
DIGITALOUTPUTS	PWL					С _{оит} =15 pF
Logical "1" Voltage	V _{OH}	2.5			V	I _{LOAD} = 1 mA
Logical "0" Voltage	V _{OH} V _{OL}	2.0		0.5	V	$I_{LOAD} = 1 \text{ mA}$
3-state Leakage		-10		10	μA	V _{OUT} = DGND to DV _{DD}
Data Valid Delay 8	l _{oz}	-10	12	10	μA ns	V OUT -DOIND TO D V DD
•	t _{DL}		5			
Data Enable Delay	t _{DEN}				ns	
Data 3-state Delay	t _{DHZ}		5		ns	

XRD87L85



ELECTRICAL CHARACTERISTICS TABLE (CONT'D) UNLESS OTHERWISE SPECIFIED: $AV_{DD} = DV_{DD} = 3.3V$, FS = 6MHZ (50% DUTY CYCLE), $V_{RT} = 2.5V$, $V_{RB} = 0.5V$, $T_{A} = 25^{\circ}C$

			25°C			
Parameter	Symbol	Min	Тур	Max	Units	Test Conditions/Comments
ACPARAMETERS						
Differential Gain Error	dg		2		%	FS = 4 x NTSC
Differential Phase Error	d_{ph}		1		Degree	FS = 4 x NTSC
POWER SUPPLIES						
Operating Voltage (AV _{DD} , DV _{DD}) ⁹	$V_{\scriptscriptstyle DD}$	3.0	3.3	3.6	V	
Current (AGND + DGND)	I _{DD}		8	12	mA	Does not include ref. current

NOTES

- 1. The difference between the measured and the ideal code width (V_{REF}/256) is the DNL error (Figure 3). The INL error is the maximum distance (in LSBs) from the best fit line to any transition voltage (Figure 4). Accuracy is a function of the sampling rate (FS).
- 2. Guaranteed, not tested
- 3. Specified values guarantee functionality. Refer to other parameters for accuracy.
- $4. 1 dB \, bandwidth \, is \, a \, measure \, of \, performance \, of \, the \, A/D \, input \, stage \, (S/H + amplifier). \, Refer \, to \, other \, parameters \, for \, accuracy \, within \, the \, specified \, bandwidth.$
- $5. \, See \, V_{\tiny IN} \, input \, equivalent \, circuit \, (Figure \, 5). \, Switched \, capacitor \, analog \, input \, requires \, driver \, with \, low \, output \, resistance.$
- 6. All inputs have diodes to DV_{DD} and DGND. Input DC currents will not exceed specified limits for any input voltage between DGND and DV_{DD} .
- 7. t_0 , t_0 should be limited to >5ns for best results.
- 8. Depends on the RC load connected to the output pin.
- $9.\,AGND\,\&\,DGND\,pins\,are\,connected\,through\,the\,silicon\,substrate.\,Connect\,together\,at\,the\,package\,and\,to\,the\,analog\,ground\,plane.$

Specifications are subject to change without notice

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C unless otherwise noted)^{1, 2, 3}

V _{DD} to GND 5.5V	Storage Temperature65 to +150°C
V_{RT} & V RBV _{DD} +0.5 to GND –0.5V	Lead Temperature (Soldering 10 seconds) +300°C
V_{IN} V_{DD} +0.5 to GND –0.5V	Package Power Dissipation Rating @ 75°C
All InputsV _{DD} +0.5 to GND -0.5V	PDIP, SOIC, SOP 675mW
All OutputsV _{DD} +0.5 to GND –0.5V	Derates above 75°C 12mW/°C

NOTES

^{1.} Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation at or above this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

^{2.} Any input pin which can see a value outside the absolute maximum ratings should be protected by Schottky diode clamps (HP5082-2835) from input pin to the supplies. All inputs have protection diodes which will protect the device from short transients outside the supplies of less than 100mA for less than 100ms.

^{3.} $V_{\rm DD}$ refers to AV $_{\rm DD}$ and DV $_{\rm DD}$. GND refers to AGND and DGND.



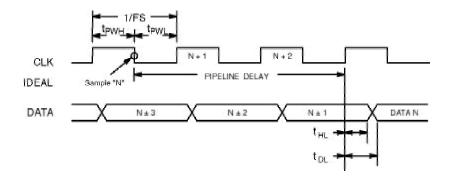


Figure 1. XRD87L85 Timing Diagram

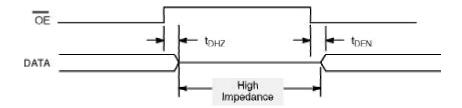


Figure 2. Output Enable/Disable Timing Diagram

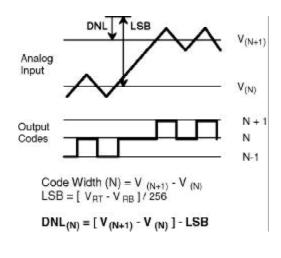
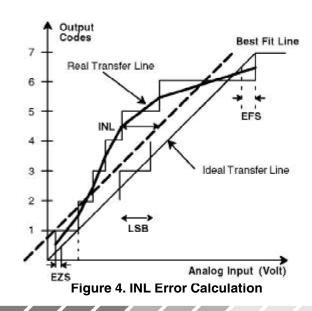


Figure 3. DNL Measurement





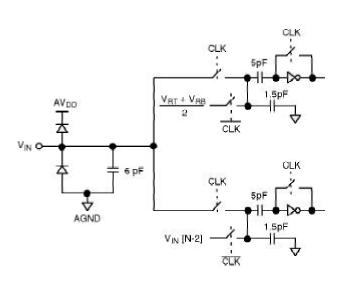


Figure 5. Equivalent Input Circuit

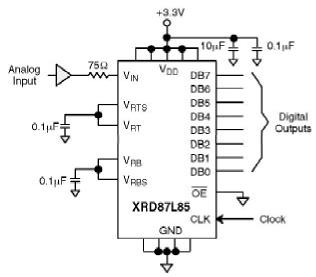


Figure 6. Typical Circuit Connections

APPLICATION NOTES

Signals should not exceed V_{DD} +0.5V or go below GND –0.5V. All pins have internal protection diodes that will protect them from short transients (<100 μ s) outside the supply range.

AGND and DGND pins are connected internally through the P-substrate. DC voltage differences between GND pins will cause undesirable internal substrate currents.

The power supply (V_{DD}) and reference voltage $(V_{RT} \& V_{RB})$ pins should be decoupled with $0.1\mu F$ and $10\mu F$ capacitors to AGND, placed as close to the chip as possible.

The digital outputs should not drive long wires or buses. The capacitive coupling and reflections will contribute noise to the conversion.

To avoid timing errors, use the rising edge of the sample clock (CLK) to latch data from the XRD87L85 to other parts of the system.

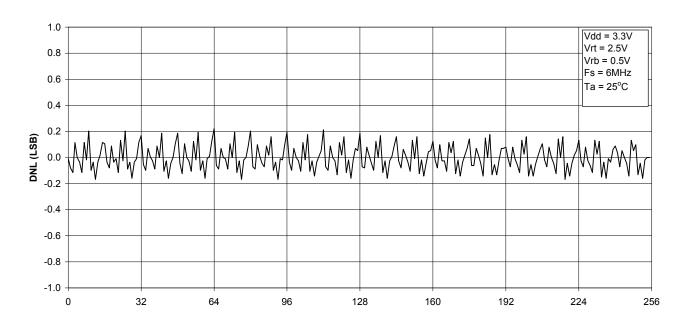
The reference can be biased internally by shorting V $_{\rm RT}$ to V $_{\rm RTS}$ and V $_{\rm RB}$ to V $_{\rm RBS}$. This will generate 0.4V at V $_{\rm RB}$ and 1.72V at V $_{\rm RT}$ (see Figure 5).

If the internal reference pins $\rm V_{RTS}$ and/or $\rm V_{RBS}$ are not used, they should be left unconnected.

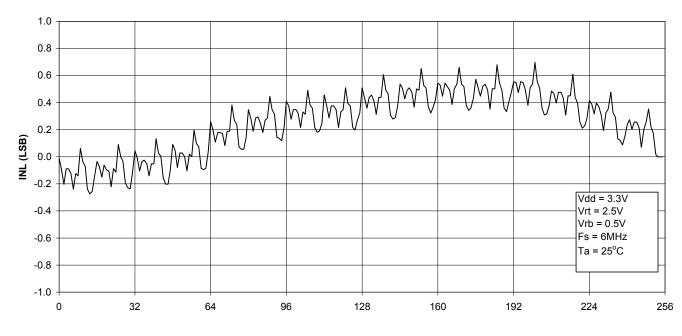
The output enable pin (\overline{OE}) should not be left unconnected. If not controlled by an active signal, then it must be tied to a logic low value.



PERFORMANCE CHARACTERISTICS

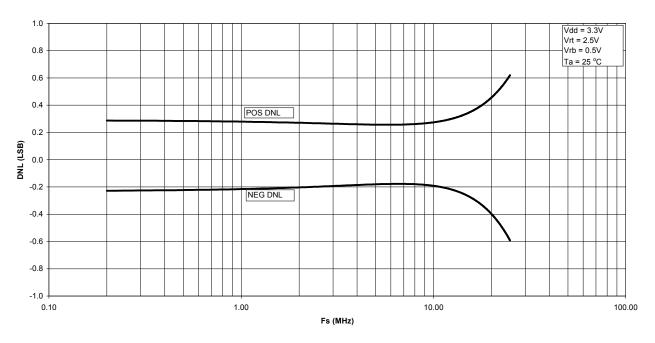


Graph 1. DNL vs. Code

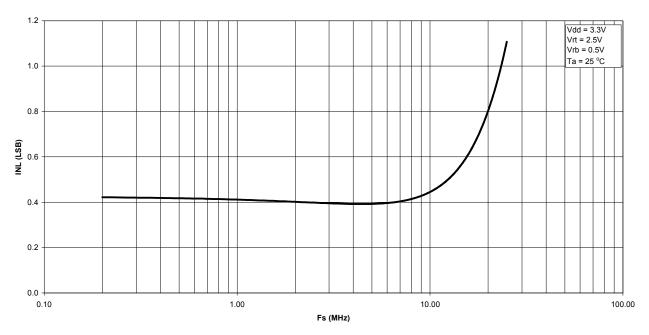


Graph 2. INL vs. Code



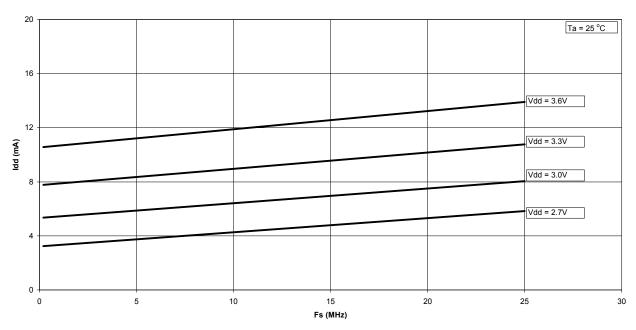


Graph 3. DNL vs. Sampling Frequency

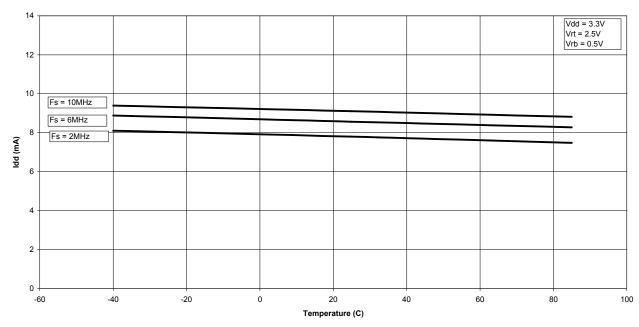


Graph 4. Best Fit INL vs. Sampling Frequency



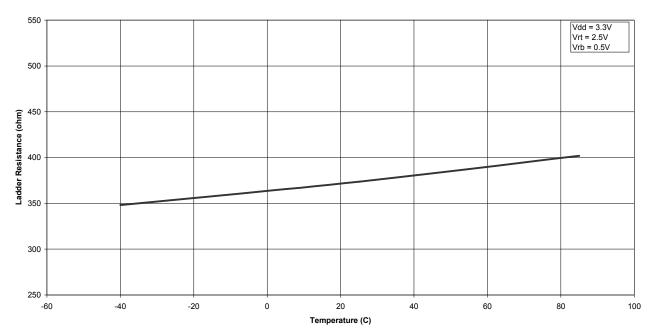


Graph 5. IDD vs. Sampling Frequency

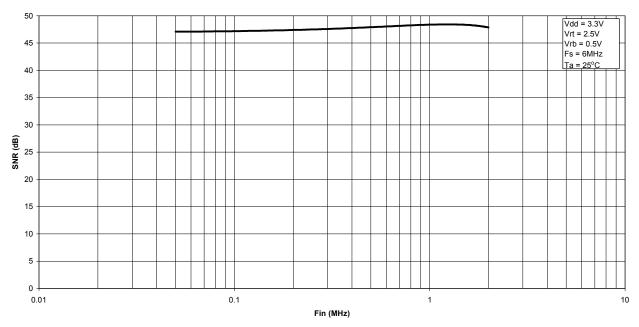


Graph 6. Supply Current vs. Temperature



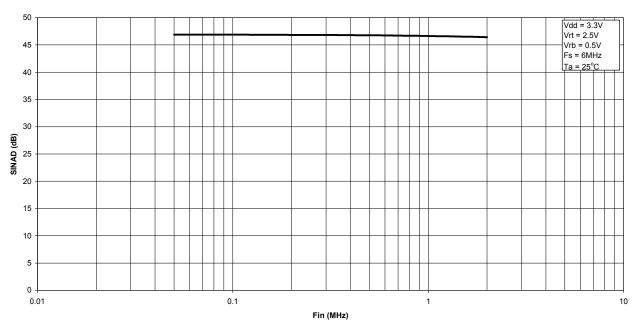


Graph 7. Ladder Resistance vs. Temperature

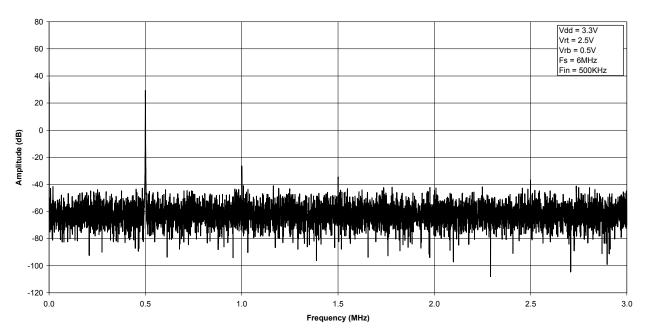


Graph 8. SNR vs. Input Frequency





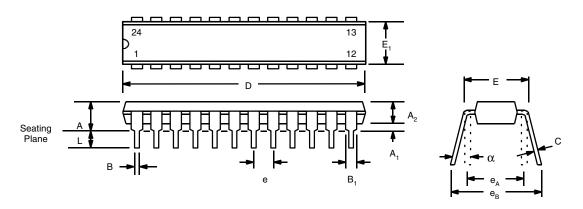
Graph 9. SINAD vs. Input Frequency



Graph 10. FFT Plot



24 LEAD PLASTIC DUAL-IN-LINE (300 MIL PDIP) REV. 1.00



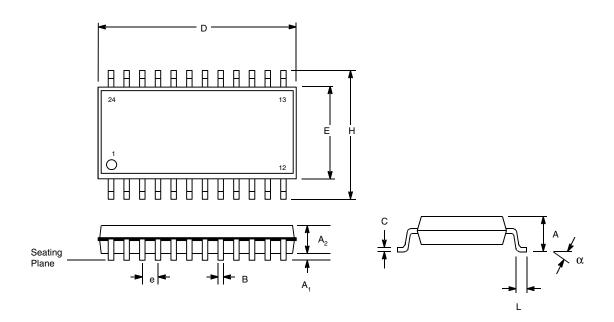
Note: The control dimension is the inch column

	INCHES		MILLIME	ΓERS	
SYMBOL	MIN	MAX	MIN	MAX	
Α	0.145	0.210	3.68	5.33	
A1	0.015	0.070	0.38	1.78	
A2	0.115	0.195	2.92	4.95	
В	0.014	0.024	0.36	0.56	
B1	0.030	0.070	0.76	1.78	
С	0.008	0.014	0.20	0.38	
D	1.125	1.275	28.58	32.39	
E	0.300	0.325	7.62	8.26	
E1	0.240	0.280	6.10	7.11	
е	0.10	00 BSC	2.54 BS	SC .	
eA	0.300 BSC		7.62 BS	SC .	
eB	0.310	0.430	7.87	10.92	
L	0.115	0.160	2.92	5.08	
а	0°	15°	0°	15°	



24 LEAD EIAJ SMALL OUTLINE (5.4 mm EIAJ SOP)

REV. 1.00

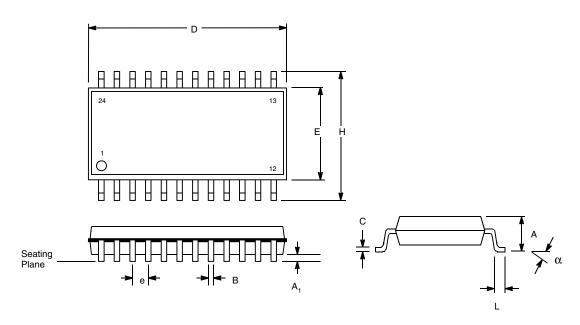


	INCHES		MILLIN	METERS
SYMBOL	MIN	MAX	MIN	MAX
Α	0.069	0.083	1.75	2.10
A1	0.002	0.008	0.05	0.20
A2	0.067	0.075	1.70	1.90
В	0.012	0.020	0.30	0.50
С	0.004	0.008	0.10	0.20
D	0.587	0.594	14.90	15.10
E	0.209	0.217	5.30	5.50
е	0.050 BSC		1.27	'BSC
Н	0.299	0.315	7.60	8.00
L	0.012	0.030	0.30	0.76
а	0°	10°	0°	10°



24 LEAD SMALL OUTLINE (300 MIL JEDEC SOIC)

REV. 1.00



	INC	HES	MILL	IMETERS
SYMBOL	MIN	MAX	MIN	MAX
Α	0.093	0.104	2.35	2.65
A1	0.004	0.012	0.10	0.30
В	0.013	0.020	0.33	0.51
С	0.009	0.013	0.23	0.32
D	0.598	0.614	15.20	15.60
E	0.291	0.299	7.40	7.60
е	0.0	50 BSC	1.27	BSC
Н	0.394	0.419	10.00	10.65
L	0.016	0.050	0.40	1.27
а	0°	8°	0°	8°



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